

## II. AMENDMENTS OF THE CLAIMS

This listing of claims replaces all prior versions, or listings of claims.

1-11. (Cancelled).

12. (Previously presented) A resistor for a semiconductor device, the resistor comprising:  
a silicide section positioned in a trough in one of a plurality of back-end-of-line (BEOL) layers; and  
a polysilicon base positioned in the trough and below the silicide section;  
wherein the silicide section has a silicidation temperature less than a damaging temperature of the plurality of BEOL layers.

13. (Original) The resistor of claim 12, wherein the silicide section includes cobalt silicide (CoSi) and has a resistivity of no less than approximately  $14\ \mu$  -ohms/cm and no greater than approximately  $20\ \mu$  -ohms/cm.

14. (Original) The resistor of claim 12, wherein the silicide section includes palladium silicide (PdSi) and has a resistivity of no less than approximately  $25\ \mu$  -ohms/cm and no greater than approximately  $30\ \mu$  -ohms/cm.

15. (Original) The resistor of claim 12, wherein the silicide section includes platinum silicide (PtSi) and has a resistivity of no less than approximately  $26\ \mu$  -ohms/cm and no greater than approximately  $35\ \mu$  -ohms/cm.

16. (Original) The resistor of claim 12, wherein the silicide section includes nickel silicide (NiSi) and has a resistivity of no less than approximately  $14\ \mu$  -ohms/cm and no greater than approximately  $20\ \mu$  -ohms/cm.
17. (Original) The resistor of claim 12, wherein the silicide section includes di-nickel silicide ( $\text{Ni}_2\text{Si}$ ) and has a resistivity of no less than approximately  $35\ \mu$  -ohms/cm and no greater than approximately  $50\ \mu$  -ohms/cm.
18. (Original) The resistor of claim 12, wherein the silicide section includes one of molybdenum silicide ( $\text{MoSi}_2$ ) and tungsten silicide ( $\text{WSi}_2$ ).
19. (Cancelled).
20. (Previously presented) A semiconductor device comprising:  
a silicide resistor in one of a plurality of back-end-of-line (BEOL) layers, the silicide resistor including a silicide section having a silicidation temperature less than a damaging temperature of the plurality of BEOL layers and a polysilicon base positioned below the silicide section;  
wherein the silicide section and the polysilicon base are positioned in a trough in one of the plurality of back-end-of-line (BEOL) layers.